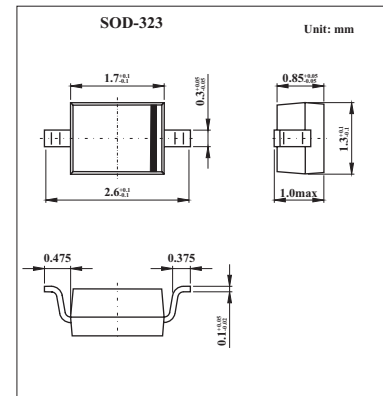


## Silicon Epitaxial Planar Diode

## MA2ZV01

## ■ Features

- Good linearity and large capacitance-ratio in  $C_D$ - $V_R$  relation
- Small series resistance  $r_D$
- S-mini type package, allowing downsizing of equipment and automatic insertion through the taping package

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Value	Unit
Reverse voltage (DC)	$V_R$	6	V
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	$I_R$	$V_R = 6\text{ V}$			10	nA
Diode capacitance	$C_{D(1V)}$	$f = 1\text{ MHz}; V_R = 1\text{ V}$	15		17	pF
	$C_{D(3V)}$	$f = 1\text{ MHz}; V_R = 3\text{ V}$	5		7	
Capacitance ratio	$C_{D(1V)}/C_{D(3V)}$		2.2			
Series resistance *	$r_s$	$V_R = 9\text{ pF}, f = 470\text{ MHz}$		1.9	1	$\Omega$

Note :

1. Rated input/output frequency: 470 MHz
2. \* : rf measuring instrument: YHP MODEL 4191A RF IMPEDANCE ANALYZER

## ■ Marking

Marking	7X
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